

SNOSAN3A - JULY 2008 - REVISED JANUARY 2009

LM119QML High Speed Dual Comparator

Check for Samples: LM119QML

FEATURES

- Available with radiation guaranteed
 - High Dose Rate 100 krad(Si)
 - ELDRS Free 100 krad(Si)
- Two independent comparators
- Operates from a single 5V supply

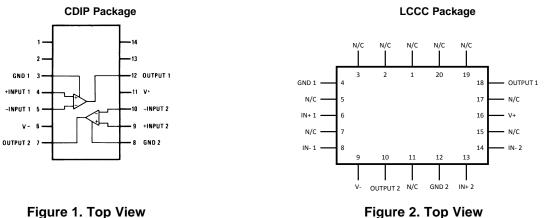
- Typically 80 ns response time at ±15V
- Minimum fan-out of 2 each side
- Maximum input current of 1 µA over temperature
- Inputs and outputs can be isolated from system ground
- High common mode slew rate

DESCRIPTION

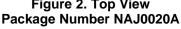
The LM119 is a precision high speed dual comparator fabricated on a single monolithic chip. It is designed to operate over a wide range of supply voltages down to a single 5V logic supply and ground. Further, it has higher gain and lower input currents than devices like the LM710. The uncommitted collector of the output stage makes the LM119 compatible with RTL, DTL and TTL as well as capable of driving lamps and relays at currents up to 25 mA.

Although designed primarily for applications requiring operation from digital logic supplies, the LM119 is fully specified for power supplies up to ±15V. It features faster response than the LM111 at the expense of higher power dissipation. However, the high speed, wide operating voltage range and low package count make the LM119 much more versatile than older devices like the LM711.

Connection Diagrams



Package Number J0014A



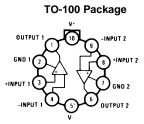


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TEXAS INSTRUMENTS

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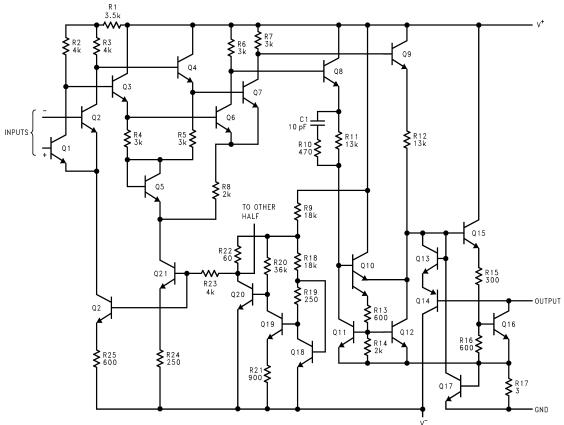


Case is connected to pin 5 (V⁻).

Figure 3. Top View Package Number LME0010C

OUTPUT 1 1 0 V+ GND 1 2 9 INPUT 2 INPUT 1+ 3 INPUT 2+ 8 INPUT 1 4 7 GND 2 V 5 0 0UTPUT 2

Figure 4. Top View Package Number NAD0010A, NAC0010A



*Do not operate the LM119 with more than 16V between GND and V⁺

These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.



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Absolute Maximum Ratings ⁽¹⁾

$36V \\ 36V \\ 25V \\ 18V \\ \pm 5V \\ \pm 15V \\ 0 mW \\ 0 sec \\ \le T_A \le 150^{\circ}C \\ \le T_A \le 125^{\circ}C \\ 50^{\circ}C \\ 260^{\circ}C \\ 0 \\ 0 \\ 0 \\ 0 \\ 0 \\ 0 \\ 0 \\ 0 \\ 0 \\ $
25V 18V $\pm 5V$ $\pm 15V$ 00 mW 0 sec $\leq T_A \leq 150^{\circ}C$ $\leq T_A \leq 125^{\circ}C$ $\leq 50^{\circ}C$
$18V$ $\pm 5V$ $\pm 15V$ 00 mW 0 sec $\leq T_A \leq 150^{\circ}\text{C}$ $\leq T_A \leq 125^{\circ}\text{C}$ 50°C
$\pm 5V$ $\pm 15V$ 00 mW 0 sec $\leq T_A \leq 150^{\circ}C$ $\leq T_A \leq 125^{\circ}C$ $\leq 50^{\circ}C$
$\pm 15V$ 20 mW 0 sec $\leq T_A \leq 150^{\circ}C$ $\leq T_A \leq 125^{\circ}C$ $\leq 50^{\circ}C$
00 mW 0 sec $\leq T_A \leq 150^{\circ}C$ $\leq T_A \leq 125^{\circ}C$ $\leq 50^{\circ}C$
0 sec $T_A \le 150^{\circ}C$ $T_A \le 125^{\circ}C$ $50^{\circ}C$
≤ T _A ≤ 150°C ≤ T _A ≤ 125°C 150°C
≤ T _A ≤ 125°C 50°C
50°C
260°C
9°C/W
3°C/W
2°C/W
8°C/W
4°C/W
2°C/W
5°C/W
32°C/W
5°C/W
32°C/W
i°C/W
1°C/W
1°C/W
3°C/W
3°C/W
TBD
TBD
TBD
TBD
25mg
800V

(1) Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is functional, but do not guarantee specific performance limits. For guaranteed specifications and test conditions, see the Electrical Characteristics. The guaranteed specifications apply only for the test conditions listed. Some performance characteristics may degrade when the device is not operated under the listed test conditions.

For supply voltages less than ±15V the absolute maximum input voltage is equal to the supply voltage. (2)

The maximum power dissipation must be derated at elevated temperatures and is dictated by T_{Jmax} (maximum junction temperature), θ_{JA} (package junction to ambient thermal resistance), and T_A (ambient temperature). The maximum allowable power dissipation at any (3) temperature is $P_{Dmax} = (T_{Jmax} - T_A)/\theta_{JA}$ or the number given in the Absolute Maximum Ratings, whichever is lower. (4) Human Body model, 1.5K Ω in series with 100pF.



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Subgroup	Description	Temp °C
1	Static tests at	25
2	Static tests at	125
3	Static tests at	-55
4	Dynamic tests at	25
5	Dynamic tests at	125
6	Dynamic tests at	-55
7	Functional tests at	25
8A	Functional tests at	125
8B	Functional tests at	-55
9	Switching tests at	25
10	Switching tests at	125
11	Switching tests at	-55
12	Settling time at	25
13	Settling time at	125
14	Settling time at	-55

(1) Mil-Std-883, Method 5005 - Group 5



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LM119/883 Electrical Characteristics DC Parameters

The following conditions apply, unless otherwise specified. $V_{CM} = 0V$

Symbol	Parameter	Conditions	Notes	Min	Max	Units	Sub- groups
+I _{CC}	Positive Supply Current	$\pm V_{CC} = \pm 15V$, $V_O = Low$			11	mA	1
		$V^+ = 5.6V$ thru $1.4K\Omega$			11.5	mA	2
-I _{CC}	Negative Supply Current	$\pm V_{CC} = \pm 15V$, $V_O = Low$		-4.2		mA	1
		$V^+ = 5.6V$ thru $1.4K\Omega$		-4.5		mA	2
I _{Leak}	Output Leakage Current	$^{+}V_{CC} = 15V, ^{-}V_{CC} = -1V,$			1.8	μΑ	1
		$V_{Gnd} = 0V, V_O = 35V,$ $V_I = 5mV$			9.5	μΑ	2
					10.0	μΑ	3
IB	Input Bias Current	$\pm V_{CC} = \pm 15V$			0.47 5	μA	1
					0.95	μA	2, 3
		$^{+}V_{CC} = 5V, ^{-}V_{CC} = 0V, V_{CM} = 1.5V$			0.47 5	μA	1
	Input Offset Voltage				.95	μΑ	2, 3
V _{IO}	Input Offset Voltage	$^{+}V_{CC} = 5V, ^{-}V_{CC} = 0V,$		-3.8	3.8	mV	1
		$V_{CM} = 1V, R_S \le 5K\Omega$		-6.8	6.8	mV	2, 3
		$^{+}V_{CC} = 5V, ^{-}V_{CC} = 0V,$		-3.8	3.8	mV	1
		$V_{CM} = 3V, R_S \le 5K\Omega$		-6.8	6.8	mV	2, 3
		$\pm V_{CC} = \pm 15V, V_{CM} = 12V,$		-3.8	3.8	mV	1
		R _S ≤ 5KΩ		-6.8	6.8	mV	2, 3
		$\pm V_{CC} = \pm 15V, V_{CM} = -12V, R_S \le 5K\Omega$		-3.8	3.8	mV	1
				-6.8	6.8	mV	2, 3
I _{IO}	Input Offset Current	$^{+}V_{CC} = 5V, ^{-}V_{CC} = 0V, V_{CM} = 1V$		-75	75	nA	1
				-100	100	nA	2, 3
		$^{+}V_{CC} = 5V, \ ^{-}V_{CC} = 0V, \ V_{CM} = 3V$		-75	75	nA	1
				-100	100	nA	2, 3
		$\pm V_{CC} = \pm 15 V$, $V_{CM} = 12 V$		-75	75	nA	1
				-100	100	nA	2, 3
		$\pm V_{CC} = \pm 15 V$, $V_{CM} = -12 V$		-75	75	nA	1
				-100	100	nA	2, 3
V _{Sat}	Output Saturation Voltage	$\pm V_{CC} = \pm 15V$, I _O = 25mA, V _I = -5mV			1.5	V	1
		$^{+}V_{CC} = 5V, ^{-}V_{CC} = 0V,$	(1)		0.4	V	1, 2
		I _O = 4.0mA	(1)		0.6	V	3
A _V	Voltage Gain	$\pm V_{CC} = \pm 15V$, Delta V _O = 12V,	(2),(3)	10.5		К	4
		$R_L = 1.4K\Omega$	(2),(3)	10		К	5, 6
		$^{+}V_{CC} = 5V, ^{-}V_{CC} = 0V,$	(2),(4)	8.0		К	4
		Delta $V_0 = 4.5V$, $R_L = 1.4K\Omega$	(2),(4)	5.0		К	5
			(2) (4)	5.8		К	6

(1) Output is monitored by measuring VI with limits from 0 to 6mV at all temperatures

(2) K = V/mV. (3) Gain is computed with an output swing from +13.5V to +1.5V.

(4) Gain is computed with an output swing from +5.0V to +0.5V.

ÈXAS **ISTRUMENTS**

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LM119-SMD Electrical Characteristics SMD 8601401 DC Parameters

The following conditions apply, unless otherwise specified. $V_{CM} = 0V$

Symbol	Parameter	Conditions	Notes	Min	Max	Units	Sub- groups
+I _{CC}	Positive Supply Current	$\pm V_{CC} = \pm 15 V$, $V_O = Low$			11	mA	1
		$V^+ = 5.6V$ thru $1.4K\Omega$			11.5	mA	2, 3
-I _{CC}	Negative Supply Current	$\pm V_{CC} = \pm 15V, V_O = Low$		-4.2		mA	1
		$V^+ = 5.6V$ thru $1.4K\Omega$		-4.5		mA	2
				-6.0		mA	3
I _{Leak}	Output Leakage Current	⁺ V _{CC} = 15V, ⁻ V _{CC} = -1V,	(1)		1.8	μA	1
		$V_{Gnd} = 0V, V_O = 35V$	(1)		10	μA	2, 3
I _{IB}	Input Bias Current	$\pm V_{CC} = \pm 15 V$			0.47 5	μA	1
					0.95	μA	2, 3
		⁺ V _{CC} = 5V	(2)		0.47 5	μA	1
			(2)		.95	μA	2, 3
V _{IO}	Input Offset Voltage	$^+V_{CC} = 5V, V_{CM} = 1V, R_S \le 5K\Omega$	(2)	-3.8	3.8	mV	1
			(2)	-6.8	6.8	mV	2, 3
		$^{+}V_{CC} = 5V, V_{CM} = 3V,$	(2)	-3.8	3.8	mV	1
		R _S ≤ 5KΩ	(2)	-6.8	6.8	mV	2, 3
		$\pm V_{CC} = \pm 15 V, V_{CM} = 12 V,$		-3.8	3.8	mV	1
		R _S ≤ 5KΩ		-6.8	6.8	mV	2, 3
		$\pm V_{CC} = \pm 15V, V_{CM} = -12V,$		-3.8	3.8	mV	1
		$R_{S} \leq 5K\Omega$		-6.8	6.8	mV	2, 3
Ю	Input Offset Current	$^{+}V_{CC} = 5V, V_{CM} = 1V$	(2)	-75	75	nA	1
			(2)	-100	100	nA	2, 3
		$^{+}V_{CC} = 5V, V_{CM} = 3V$	(2)	-75	75	nA	1
			(2)	-100	100	nA	2, 3
		$\pm V_{CC} = \pm 15V, V_{CM} = 12V$		-75	75	nA	1
				-100	100	nA	2, 3
		$\pm V_{CC} = \pm 15V, V_{CM} = -12V$		-75	75	nA	1
				-100	100	nA	2, 3
VI	Input Voltage Range	$^{+}V_{CC} = 5V$	(2), (3)	1.0	3.0	V	1, 2, 3
		$\pm V_{CC} = \pm 15V$	(3)	-12	12	V	1, 2, 3
V _{Sat}	Output Saturation Voltage	$\pm V_{CC} = \pm 15V$, $I_0 = 25mA$, $V_1 \le -5mV$	(1)		1.5	V	1, 2, 3
		$^{+}V_{CC} = 3.5V, ^{-}V_{CC} = -1V,$			0.4	V	1, 2
		$V_{I} \leq -6mV, I_{O} \leq 3.2mA$			0.6	V	3
A _V	Voltage Gain	$\pm V_{CC} = \pm 15V$, Delta V _O = 12V,	(4)	10.5		К	4
		$R_L = 1.4K\Omega$	(4)	10		К	5, 6
		$^{+}V_{CC} = 5V, ~V_{CC} = 0V,$	(2), (4)	8.0		К	4
		Delta $V_0 = 4.5V$, $R_L = 1.4K\Omega$	(2), (4)	5.0		К	5
			(2), (4)	5.8		К	6
CMRR	Common Mode Rejection Ratio	$\pm V_{CC} = \pm 15V, V_{CM} = \pm 12V$		80		dB	4

 $\begin{array}{ll} (1) & V_{I} \geq 8mV \text{ at extremes for } I_{Leak} \text{ and } V_{I} \leq -8mV \text{ at extremes for } V_{Sat} \ (V_{I} \text{ to exceed } V_{OS}. \\ (2) & 5V \text{ differential across } +V_{CC} \text{ and } -V_{CC}. \\ (3) & \text{Parameter guaranteed by } V_{IO} \text{ and } I_{IO} \text{ tests.} \\ (4) & K = V/mV. \end{array}$



LM119 Electrical Characteristics SMD 5962-9679801, HIGH DOSE RATE DC Parameters

The following conditions apply, unless otherwise specified. $V_{CM} = 0V$

Symbol	Parameter	Conditions	Notes	Min	Max	Units	Sub- groups
+l _{CC}	Positive Supply Current	$\pm V_{CC} = \pm 15 V, V_O = Low$			11	mA	1
		$V^+ = 5.6V$ thru $1.4K\Omega$			11.5	mA	2, 3
-I _{CC}	Negative Supply Current	$\pm V_{CC} = \pm 15 V, V_O = Low$		-4.2		mA	1
		$V^+ = 5.6V$ thru $1.4K\Omega$		-4.5		mA	2
				-6.0		mA	3
I _{Leak}	Output Leakage Current	$^{+}V_{CC} = 15V, \ ^{-}V_{CC} = -1V,$	(1)		1.8	μA	1
		$V_{Gnd} = 0V, V_O = 35V$	(1)		10	μA	2, 3
I _{IB}	Input Bias Current	$\pm V_{CC} = \pm 15 V$			0.47 5	μA	1
					0.95	μΑ	2, 3
		$^+V_{CC} = 5V$	(2)		0.47 5	μA	1
			(2)		.95	μA	2, 3
V _{IO}	Input Offset Voltage	$^{+}V_{CC} = 5V, V_{CM} = 1V, R_{S} \le 5K\Omega$	(2)	-3.8	3.8	mV	1
			(2)	-6.8	6.8	mV	2, 3
		$^{+}V_{CC} = 5V, V_{CM} = 3V,$	(2)	-3.8	3.8	mV	1
		R _S ≤ 5KΩ	(2)	-6.8	6.8	mV	2, 3
		$\pm V_{CC} = \pm 15V, V_{CM} = 12V,$		-3.8	3.8	mV	1
		R _S ≤ 5KΩ		-6.8	6.8	mV	2, 3
		$\pm V_{CC} = \pm 15V, V_{CM} = -12V,$		-3.8	3.8	mV	1
		$R_S \le 5K\Omega$		-6.8	6.8	mV	2, 3
lio	Input Offset Current	$^{+}V_{CC} = 5V, V_{CM} = 1V$	(2)	-75	75	nA	1
			(2)	-100	100	nA	2, 3
		$^{+}V_{CC} = 5V, V_{CM} = 3V$	(2)	-75	75	nA	1
			(2)	-100	100	nA	2, 3
		$\pm V_{CC} = \pm 15V, V_{CM} = 12V$		-75	75	nA	1
				-100	100	nA	2, 3
		$\pm V_{CC} = \pm 15V, V_{CM} = -12V$		-75	75	nA	1
				-100	100	nA	2, 3
VI	Input Voltage Range	$^{+}V_{CC} = 5V$	(2), (3)	1.0	3.0	V	1, 2, 3
		$\pm V_{CC} = \pm 15V$	(3)	-12	12	V	1, 2, 3
V _{Sat}	Output Saturation Voltage	$\pm V_{CC} = \pm 15V$, $I_0 = 25mA$, $V_1 \le -5mV$	(1)		1.5	V	1, 2, 3
		$^{+}V_{CC} = 3.5V, \ ^{-}V_{CC} = -1V,$			0.4	V	1, 2
		$V_{I} \le -6mV, I_{O} \le 3.2mA$			0.6	V	3
A _V	Voltage Gain	$\pm V_{CC} = \pm 15V$, Delta V _O = 12V,	(4)	10.5		К	4
		$R_L = 1.4K\Omega$	(4)	10		К	5, 6
		$^{+}V_{CC} = 5V, ^{-}V_{CC} = 0V,$ Delta $V_{O} = 4.5V, R_{L} = 1.4K\Omega$	(2), (4)	8.0		К	4
		Delta V _O = 4.5V, R _L = 1.4 K Ω	(2), (4)	5.0		К	5
			(2), (4)	5.8		К	6
CMRR	Common Mode Rejection Ratio	$\pm V_{CC} = \pm 15 V, V_{CM} = \pm 12 V$		80	T	dB	4

 $\begin{array}{ll} (1) & V_{I} \geq 8mV \text{ at extremes for } I_{Leak} \text{ and } V_{I} \leq -8mV \text{ at extremes for } V_{Sat} \ (V_{I} \text{ to exceed } V_{OS}. \\ (2) & 5V \text{ differential across } +V_{CC} \text{ and } -V_{CC}. \\ (3) & \text{Parameter guaranteed by } V_{IO} \text{ and } I_{IO} \text{ tests.} \\ (4) & K = V/mV. \end{array}$

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SMD 5962-9679801, HIGH DOSE RATE DC DELTA Parameters

The following conditions apply, unless otherwise specified.

 $V_{CM} = 0V$, Delta calculations performed on QMLV devices at group B, subgroup 5 only.

Symbol	Parameter	Conditions	Notes	Min	Max	Units	Sub- groups
+I _{CC}	Positive Supply Current	$\pm V_{CC} = \pm 15V$, $V_O = Low$ $V^+ = 5.6V$ thru $1.4K\Omega$		-1.0	1.0	mA	1
-I _{CC}	Negative Supply Current	$\pm V_{CC} = \pm 15V$, $V_O = Low$ $V^+ = 5.6V$ thru $1.4K\Omega$		-0.5	0.5	mA	1
V _{IO}	Input Offset Voltage	⁺ V _{CC} = 5V, V _{CM} = 1V, R _S ≤ 5KΩ		-0.4	0.4	mV	1

SMD 5962-9679801, High Dose Rate 100K Post Radiation Parameters @ 25°C ⁽¹⁾

The following conditions apply, unless otherwise specified. $V_{CM} = 0V$

Symbol	Parameter	Conditions	Notes	Min	Max	Units	Sub- groups
I _{IB}	Input Bias Current	$\pm V_{CC} = \pm 15V$			1.0	μA	1
		$V_{CC} = 5V$			1.0	μA	1
V _{IO}	Input Offset Voltage	$^+V_{CC} = 5V, V_{CM} = 1V, R_S \le 5K\Omega$		-4.0	4.0	mV	1
		$^+V_{CC} = 5V, V_{CM} = 3V, R_S \le 5K\Omega$		-4.0	4.0	mV	1
		$\pm V_{CC} = \pm 15V, V_{CM} = 12V, R_S \le 5K\Omega$		-4.0	4.0	mV	1
		$\pm V_{CC} = \pm 15V, V_{CM} = -12V, R_S \le 5K\Omega$		-4.0	4.0	mV	1

(1) Pre and post irradiation limits are identical to those listed under AC and DC electrical characteristics except as listed in the Post Radiation Limits Table. These parts may be dose rate sensitive in a space environment and demonstrate enhanced low dose rate sensitivity. Radiation end point limits for the noted parameters are guaranteed only for the conditions as specified in MIL-STD-883, per Test Method 1019, Condition A.

LM119 Electrical Characteristics SMD 5962-9679802, ELDRS FREE DC Parameters

The following conditions apply, unless otherwise specified. $V_{CM} = 0V$

Symbol	Parameter	Conditions	Notes	Min	Мах	Units	Sub- groups
+I _{CC}	Positive Supply Current	$\pm V_{CC} = \pm 15V, V_O = Low$			11	mA	1
		$V^+ = 5.6V$ thru $1.4K\Omega$			11.5	mA	2, 3
-I _{CC}	Negative Supply Current	$\pm V_{CC} = \pm 15V, V_O = Low$		-4.2		mA	1
		$V^+ = 5.6V$ thru $1.4K\Omega$		-4.5		mA	2
				-6.0		mA	3
I _{Leak}	Output Leakage Current	ye Current ${}^+V_{CC} = 15V, {}^-V_{CC} = -1V, V_{Gnd} = 0V, V_O = 35V$	(1)		1.8	μA	1
		$V_{Gnd} = 0V, V_O = 35V$	(1)		10	μA	2, 3
I _{IB}	Input Bias Current	$\pm V_{CC} = \pm 15V$			0.47 5	μA	1
					0.95	μA	2, 3
		$^{+}V_{CC} = 5V$	(2)		0.47 5	μΑ	1
			(2)		.95	μA	2, 3

(1) $V_I \ge 8mV$ at extremes for I_{Leak} and $V_I \le -8mV$ at extremes for V_{Sat} (V_I to exceed V_{OS} .

(2) 5V differential across +V_{CC} and -V_{CC}.



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LM119 Electrical Characteristics SMD 5962-9679802, ELDRS FREE DC Parameters (continued)

The following conditions apply, unless otherwise specified. $V_{CM} = 0V$

Symbol	Parameter	Conditions	Notes	Min	Max	Units	Sub- groups
V _{IO}	Input Offset Voltage	$^+V_{CC} = 5V, V_{CM} = 1V, R_S \le 5K\Omega$	(2)	-3.8	3.8	mV	1
			(2)	-6.8	6.8	mV	2, 3
		$^{+}V_{CC} = 5V, V_{CM} = 3V,$	(2)	-3.8	3.8	mV	1
		R _S ≤ 5KΩ	(2)	-6.8	6.8	mV	2, 3
		$\pm V_{CC} = \pm 15V, V_{CM} = 12V,$		-3.8	3.8	mV	1
		R _S ≤ 5KΩ		-6.8	6.8	mV	2, 3
		$\pm V_{CC} = \pm 15 V, V_{CM} = -12 V,$		-3.8	3.8	mV	1
		$R_{S} \le 5K\Omega$		-6.8	6.8	mV	2, 3
l _{io}	Input Offset Current	$^{+}V_{CC} = 5V, V_{CM} = 1V$	(2)	-75	75	nA	1
			(2)	-100	100	nA	2, 3
		$^{+}V_{CC} = 5V, V_{CM} = 3V$	(2)	-75	75	nA	1
			(2)	-100	100	nA	2, 3
		$\pm V_{CC} = \pm 15 V, V_{CM} = 12 V$		-75	75	nA	1
				-100	100	nA	2, 3
		$\pm V_{CC} = \pm 15V, V_{CM} = -12V$		-75	75	nA	1
				-100	100	nA	2, 3
VI	Input Voltage Range	$^{+}V_{CC} = 5V$	(3), (3)	1.0	3.0	V	1, 2, 3
		$\pm V_{CC} = \pm 15V$	(3)	-12	12	V	1, 2, 3
V _{Sat}	Output Saturation Voltage	$\pm V_{CC} = \pm 15V$, $I_O = 25mA$, $V_I \le -5mV$	(1)		1.5	V	1, 2, 3
		$^{+}V_{CC} = 3.5V, ^{-}V_{CC} = -1V,$			0.4	V	1, 2
		$V_1 \le -6mV, I_0 \le 3.2mA$			0.6	V	3
A _V	Voltage Gain	$\pm V_{CC} = \pm 15 V$, Delta V _O = 12V,	(4)	10.5		К	4
		$R_L = 1.4K\Omega$	(4)	10		К	5, 6
		$^{+}V_{CC} = 5V, ^{-}V_{CC} = 0V,$	(5), (4)	8.0		К	4
		Delta $V_0 = 4.5V$, $R_L = 1.4K\Omega$	(5), (4)	5.0		К	5
			(5), (4)	5.8		К	6
CMRR	Common Mode Rejection Ratio	$\pm V_{CC} = \pm 15V, V_{CM} = \pm 12V$		80		dB	4

(3) Parameter guaranteed by V_{IO} and I_{IO} tests.

(4) K = V/mV.

(5) 5V differential across +V_{CC} and -V_{CC}.

SMD 5962-9679802, ELDRS FREE DC DELTA Parameters

The following conditions apply, unless otherwise specified.

 V_{CM} = 0V, Delta calculations performed on QMLV devices at group B, subgroup 5 only.

Symbol	Parameter	Conditions	Notes	Min	Мах	Units	Sub- groups
+I _{CC}	Positive Supply Current	$\pm V_{CC} = \pm 15V$, $V_O = Low$ $V^+ = 5.6V$ thru 1.4K Ω		-1.0	1.0	mA	1
-I _{CC}	Negative Supply Current	$\pm V_{CC} = \pm 15V$, $V_O = Low$ $V^+ = 5.6V$ thru 1.4K Ω		-0.5	0.5	mA	1
V _{IO}	Input Offset Voltage	$^+V_{CC} = 5V, V_{CM} = 1V, R_S \le 5K\Omega$		-0.4	0.4	mV	1

STRUMENTS

EXAS

SMD 5962-9679802, ELDRS FREE 100K Post Radiation Parameters @ 25°C (1)

The following conditions apply, unless otherwise specified. $V_{CM} = 0V$

Symbol	Parameter	Conditions	Notes	Min	Max	Units	Sub- groups
I _{IB}	Input Bias Current	$\pm V_{CC} = \pm 15V$			1.0	μA	1
		$V_{CC} = 5V$			1.0	μA	1
V _{IO}	Input Offset Voltage	⁺ $V_{CC} = 5V, V_{CM} = 1V, R_S \le 5K\Omega$		-4.0	4.0	mV	1
		$^+V_{CC} = 5V, V_{CM} = 3V, R_S \le 5K\Omega$		-4.0	4.0	mV	1
		$\pm V_{CC} = \pm 15V, V_{CM} = 12V, R_S \le 5K\Omega$		-4.0	4.0	mV	1
		$\pm V_{CC} = \pm 15V, V_{CM} = -12V, R_S \le 5K\Omega$		-4.0	4.0	mV	1

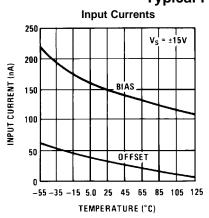
(1) Pre and post irradiation limits are identical to those listed under AC and DC electrical characteristics except as listed in the Post Radiation Limits Table. Low dose rate testing has been performed on a wafer-by-wafer basis, per Test Method 1019, Condition D of MIL-STD-883, with no enhanced low dose rate sensitivity (ELDRS).

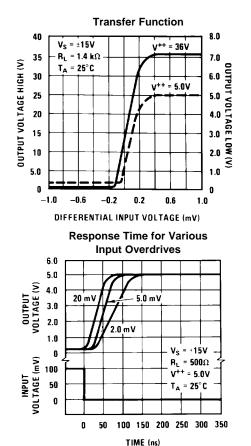
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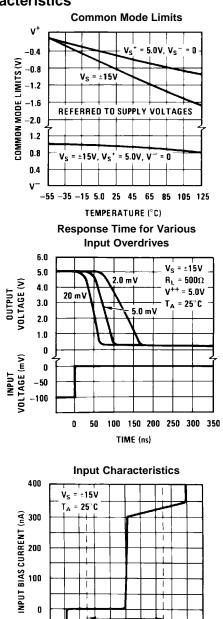


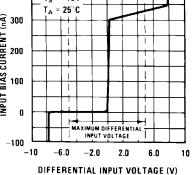
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Typical Performance Characteristics





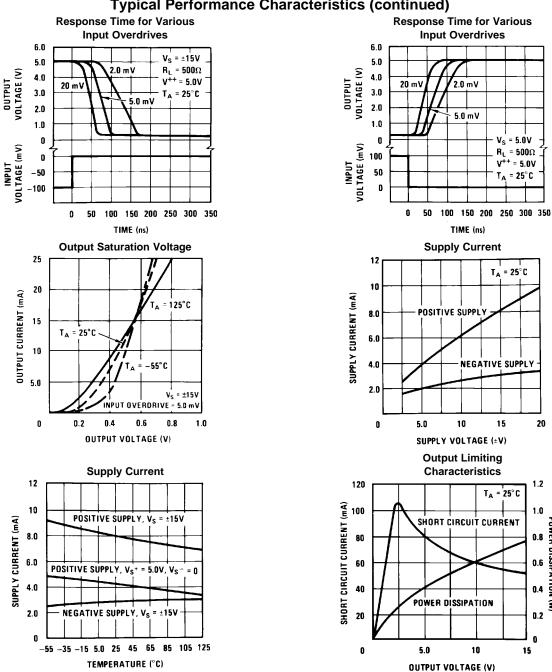




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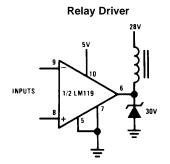
POWER DISSIPATION

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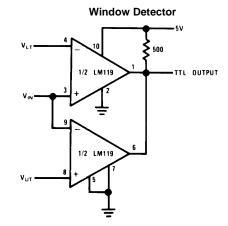


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TYPICAL APPLICATIONS



Pin numbers are for LME0010C package.



 $\begin{aligned} V_{OUT} &= 5V \text{ for } V_{LT} \leq V_{IN} \leq V_{UT} \\ V_{OUT} &= 0 \text{ for } V_{IN} \leq V_{LT} \text{ or } V_{IN} \geq V_{UT} \end{aligned}$

LM119QML

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REVISION HISTORY

Date Released	Revision	Section	Originator	Changes
07/24/08	A	New release to corporate format	L. Lytle	2 MDS datasheets converted into one corporate data sheet format. Added Radiation information. MDS data sheets MNLM119-X Rev. 0F1 & MDLM119-X Rev 2A2 will be archived.
01/13/09	В	Features, Ordering Info., Electrical Section, Notes 13 and 14	Larry McGee	Added reference to ELDRS and Die NSID's to data sheet. Correction from: 100k rd(Si) to 100 krad(Si) in ordering info. Changed wording in Notes 13 and 14 Revision A will be Archived.



PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish	MSL Peak Temp (3)	Op Temp (°C)	Top-Side Markings	Samples
5962-9679801VCA	ACTIVE	CDIP	J	14	25	TBD	A42 SNPB	Level-1-NA-UNLIM	-55 to 125	LM119J-QMLV 5962-9679801VCA Q	Samples
5962-9679801VIA	ACTIVE	TO-100	LME	10	20	TBD	POST-PLATE	Level-1-NA-UNLIM	-55 to 125	LM119H-QMLV 5962-9679801VIA Q ACO 5962-9679801VIA Q >T	Samples
5962R9679801VCA	ACTIVE	CDIP	J	14	25	TBD	A42 SNPB	Level-1-NA-UNLIM	-55 to 125	LM119JRQMLV 5962R9679801VCA Q	Samples
5962R9679801VHA	ACTIVE	CLGA	NAD	10	19	TBD	A42 SNPB	Level-1-NA-UNLIM	-55 to 125	LM119W RQMLV Q 5962R96798 01VHA ACO 01VHA >T	Samples
5962R9679801VIA	ACTIVE	TO-100	LME	10	20	TBD	POST-PLATE	Level-1-NA-UNLIM	-55 to 125	LM119HRQMLV 5962R9679801VIA Q ACO 5962R9679801VIA Q >T	Samples
5962R9679801VXA	ACTIVE	CLGA	NAC	10	54	TBD	Call TI	Level-1-NA-UNLIM	-55 to 125	LM119WG RQMLV Q 5962R96798 01VXA ACO 01VXA >T	Samples
5962R9679802VCA	ACTIVE	CDIP	J	14	25	TBD	A42 SNPB	Level-1-NA-UNLIM	-55 to 125	LM119JRLQMLV 5962R9679802VCA Q	Samples
5962R9679802VHA	ACTIVE	CLGA	NAD	10	19	TBD	A42 SNPB	Level-1-NA-UNLIM	-55 to 125	LM119W RLQMLV Q 5962R96798 02VHA ACO 02VHA >T	Samples
5962R9679802VIA	ACTIVE	TO-100	LME	10	20	TBD	Call TI	Call TI	-55 to 125	LM119HRLQMLV 5962R9679802VIA Q ACO 5962R9679802VIA Q >T	Samples
5962R9679802VXA	ACTIVE	CLGA	NAC	10	54	TBD	A42 SNPB	Level-1-NA-UNLIM	-55 to 125	LM119WG RLQMLV Q 5962R96798 02VXA ACO 02VXA >T	Samples
86014012A	ACTIVE	LCCC	NAJ	20	50	TBD	POST-PLATE	Level-1-NA-UNLIM	-55 to 125	LM119E -SMD Q	Samples

PACKAGE OPTION ADDENDUM



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26-Jan-2013

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)		Sample
	(1)		Drawing			(2)		(3)	-	(4) 5962-86014 012A ACO 012A >T	-
8601401CA	ACTIVE	CDIP	J	14	25	TBD	A42 SNPB	Level-1-NA-UNLIM	-55 to 125	LM119J-SMD 5962-8601401CA Q	Sample
8601401HA	ACTIVE	CLGA	NAD	10	19	TBD	A42 SNPB	Level-1-NA-UNLIM	-55 to 125	LM119W -SMD Q 5962-86014 01HA ACO 01HA >T	Sampl
8601401IA	ACTIVE	TO-100	LME	10	20	TBD	POST-PLATE	Level-1-NA-UNLIM	-55 to 125	LM119H-SMD 5962-8601401IA Q ACO 5962-8601401IA Q >T	Sampl
LM119E-SMD	ACTIVE	LCCC	NAJ	20	50	TBD	POST-PLATE	Level-1-NA-UNLIM	-55 to 125	LM119E -SMD Q 5962-86014 012A ACO 012A >T	Sampl
LM119E/883	ACTIVE	LCCC	NAJ	20	50	TBD	POST-PLATE	Level-1-NA-UNLIM	-55 to 125	LM119E /883 Q ACO /883 Q >T	Sampl
LM119H-QMLV	ACTIVE	TO-100	LME	10	20	TBD	POST-PLATE	Level-1-NA-UNLIM	-55 to 125	LM119H-QMLV 5962-9679801VIA Q ACO 5962-9679801VIA Q >T	Sampl
LM119H-SMD	ACTIVE	TO-100	LME	10	20	TBD	POST-PLATE	Level-1-NA-UNLIM	-55 to 125	LM119H-SMD 5962-8601401IA Q ACO 5962-8601401IA Q >T	Sampl
LM119H/883	ACTIVE	TO-100	LME	10	20	TBD	POST-PLATE	Level-1-NA-UNLIM	-55 to 125	LM119H/883 Q ACO LM119H/883 Q >T	Sampl
LM119HRLQMLV	ACTIVE	TO-100	LME	10	20	TBD	Call TI	Call TI	-55 to 125	LM119HRLQMLV 5962R9679802VIA Q ACO 5962R9679802VIA Q >T	Sampl
LM119HRQMLV	ACTIVE	TO-100	LME	10	20	TBD	POST-PLATE	Level-1-NA-UNLIM	-55 to 125	LM119HRQMLV 5962R9679801VIA Q ACO 5962R9679801VIA Q ≻T	Sampl
LM119J-QMLV	ACTIVE	CDIP	J	14	25	TBD	A42 SNPB	Level-1-NA-UNLIM	-55 to 125	LM119J-QMLV 5962-9679801VCA Q	Sampl
LM119J-SMD	ACTIVE	CDIP	J	14	25	TBD	A42 SNPB	Level-1-NA-UNLIM	-55 to 125	LM119J-SMD	Sampl

PACKAGE OPTION ADDENDUM



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Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish	MSL Peak Temp (3)	Op Temp (°C)	Top-Side Markings (4) 5962-8601401CA Q	Samples
LM119J/883	ACTIVE	CDIP	J	14	25	TBD	A42 SNPB	Level-1-NA-UNLIM	-25 to 85	LM119J/883 Q	Samples
LM119JRLQMLV	ACTIVE	CDIP	J	14	25	TBD	A42 SNPB	Level-1-NA-UNLIM	-55 to 125	LM119JRLQMLV 5962R9679802VCA Q	Sample
LM119JRQMLV	ACTIVE	CDIP	J	14	25	TBD	A42 SNPB	Level-1-NA-UNLIM	-55 to 125	LM119JRQMLV 5962R9679801VCA Q	Sample
LM119W-SMD	ACTIVE	CLGA	NAD	10	19	TBD	A42 SNPB	Level-1-NA-UNLIM	-55 to 125	LM119W -SMD Q 5962-86014 01HA ACO 01HA >T	Sample
LM119W/883	ACTIVE	CLGA	NAD	10	19	TBD	A42 SNPB	Level-1-NA-UNLIM	-55 to 125	LM119W /883 Q ACO /883 Q >T	Sample
LM119WGRLQMLV	ACTIVE	CLGA	NAC	10	54	TBD	A42 SNPB	Level-1-NA-UNLIM	-55 to 125	LM119WG RLQMLV Q 5962R96798 02VXA ACO 02VXA >T	Sample
LM119WGRQMLV	ACTIVE	CLGA	NAC	10	54	TBD	Call TI	Level-1-NA-UNLIM	-55 to 125	LM119WG RQMLV Q 5962R96798 01VXA ACO 01VXA >T	Sample
LM119WRLQMLV	ACTIVE	CLGA	NAD	10	19	TBD	A42 SNPB	Level-1-NA-UNLIM	-55 to 125	LM119W RLQMLV Q 5962R96798 02VHA ACO 02VHA >T	Sample
LM119WRQMLV	ACTIVE	CLGA	NAD	10	19	TBD	A42 SNPB	Level-1-NA-UNLIM	-55 to 125	LM119W RQMLV Q 5962R96798 01VHA ACO 01VHA >T	Sample

⁽¹⁾ The marketing status values are defined as follows: **ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.



26-Jan-2013

PREVIEW: Device has been announced but is not in production. Samples may or may not be available. **OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ Only one of markings shown within the brackets will appear on the physical device.

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OTHER QUALIFIED VERSIONS OF LM119QML, LM119QML-SP :

Military: LM119QML

• Space: LM119QML-SP

NOTE: Qualified Version Definitions:

- Military QML certified for Military and Defense Applications
- Space Radiation tolerant, ceramic packaging and qualified for use in Space-based application

J (R-GDIP-T**) 14 LEADS SHOWN

CERAMIC DUAL IN-LINE PACKAGE

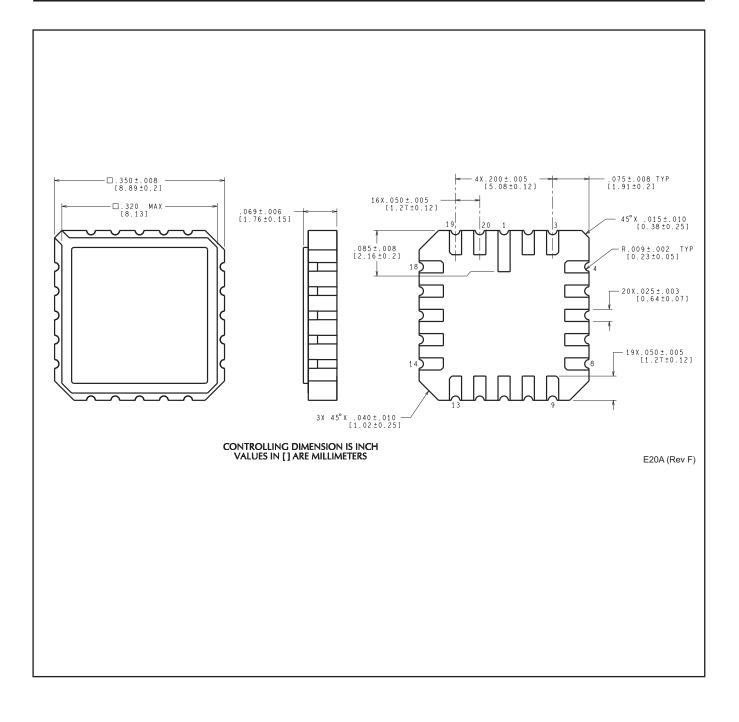


NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- C. This package is hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification only on press ceramic glass frit seal only.
- E. Falls within MIL STD 1835 GDIP1-T14, GDIP1-T16, GDIP1-T18 and GDIP1-T20.

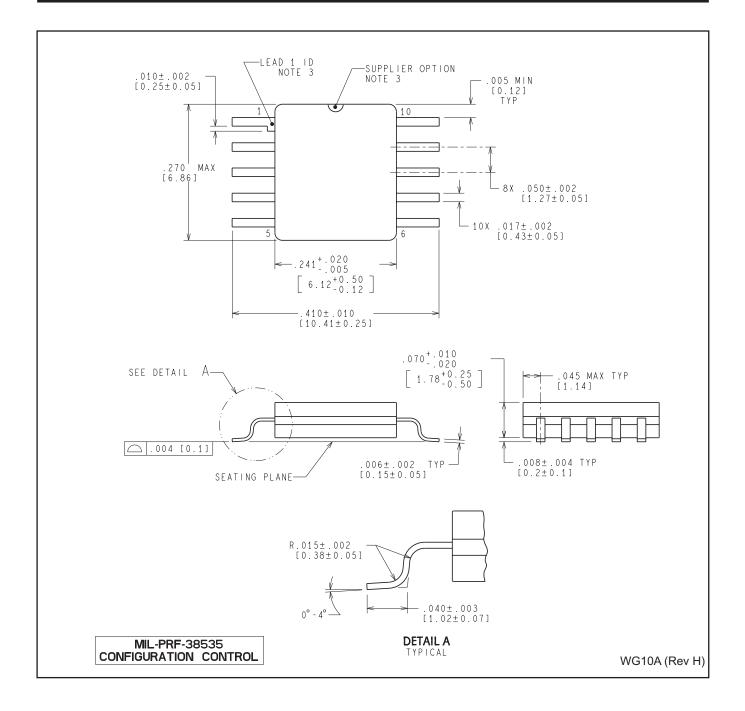
MECHANICAL DATA

NAJ0020A

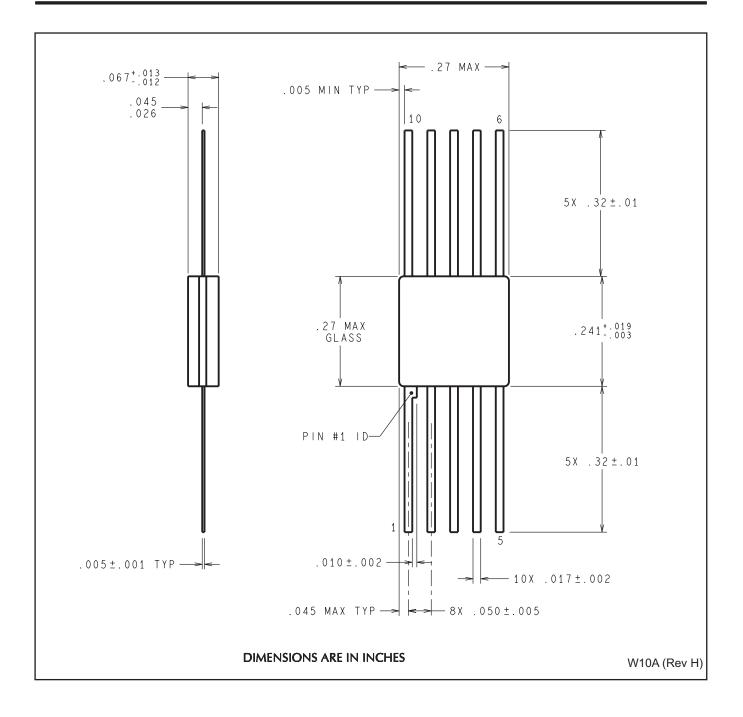




NAC0010A



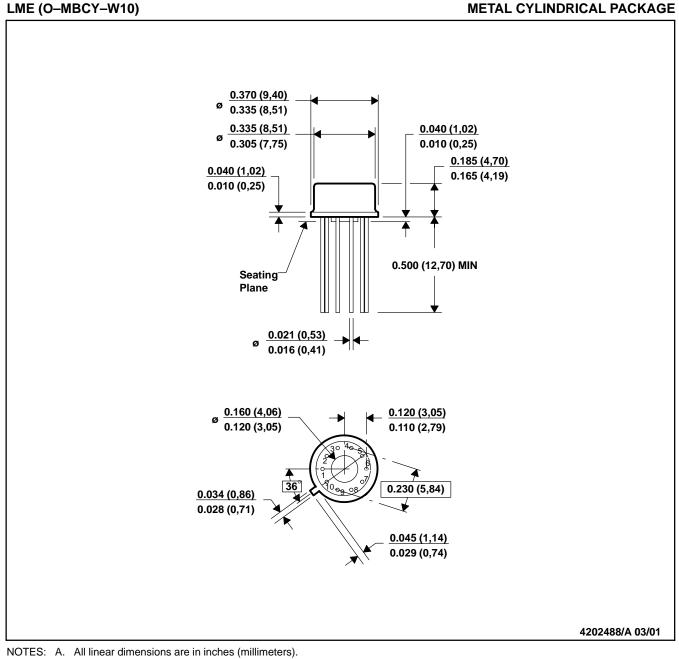
NAD0010A





MECHANICAL DATA

MMBC006 - MARCH 2001



- B. This drawing is subject to change without notice.
- C. Leads in true position within 0.010 (0,25) R @ MMC at seating plane.
- D. Pin numbers shown for reference only. Numbers may not be marked on package.
- E. Falls within JEDEC MO-006/TO-100.



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